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The FAMES Payoff Begins: Discover Key FAMES Results

At CEA-Leti's LID World Summit 2026 in Grenoble

'The Pilot Line Has Reached a Pivotal Stage, With Highly Innovative Results'

GRENOBLE, France – June 4, 2026 – Halfway through its five-year project to boost European technical sovereignty in critical semiconductor technologies, the FAMES Pilot Line will present its early key breakthroughs June 24 at the [CEA-Leti LID World Summit 2026](#) in Grenoble.

The half-day workshop, "[The FAMES Payoff Begins](#)", features major results in the areas of FD-SOI advanced nodes, embedded NVMs, 3D integration, RF components, and power-management IC solutions. Organized by the FAMES Academy, which was launched at last June's CEA-Leti LID World Summit to set up the pilot line's periodic training programs, the session marks a critical transition for the pilot line project: moving from experimental validation to industrial readiness.

Strengthening Partnerships and Feeding Key Initiatives

"The FAMES pilot line has reached a pivotal stage, with highly innovative results obtained on all developed technologies," said Dominique Noguet, coordinator of the pan-European initiative and CEA-Leti vice president. "These outcomes are strengthening FAMES partnerships and feeding other FAMES key initiatives, such as our open-access and training programs."

Reshaping the Landscape for AI Factories, IoT, and Secure Edge Computing

The session will unveil the first tangible results from the FAMES Pilot Line, which [officially inaugurated](#) its state-of-the-art cleanroom earlier this year. Attendees will gain exclusive insights into breakthrough technologies that are reshaping the landscape for AI factories, IoT, and secure edge computing, including:

- **State-of-the-Art Infrastructure:** How to design and build a sustainable and flexible cleanroom adapted to new generation of process equipment.
- **Process Scaling:** Key architectural building blocks driving the 10nm FD-SOI node, including advanced strain engineering and self-aligned double patterning (SADP) techniques.

- **Next-Gen Memory:** The world's first demonstration of a scalable Hf_{0.5}Zr_{0.5}O₂ (HZO) based ferroelectric capacitor platform integrated into the back-end-of-line (BEOL) at the 22nm FD-SOI node, positioning FeRAM as a competitive solution for embedded applications.
- **Advanced RF:** New bulk acoustic wave (BAW) filter solutions adapted for the emerging FR3 frequency range (7.125 – 24.25 GHz), bridging the gap between sub-6 GHz and millimeter-wave technologies.
- **Hardware Security:** A deep dive into "invisible walls" for cybersecurity, showcasing how FD-SOI and new memory implementation enable polymorphic hardware obfuscation and physical unclonable functions (PUFs) to resist side-channel attacks and counterfeiting.
- **Open Access:** An introduction of the recently opened topics for 2026, and a dedicated focus on the availability of the pathfinding design kit to evaluate the performance of the 10nm FD-SOI CMOS technology.
- **Empowering the Ecosystem:** Beyond the technical showcases, the workshop will formalize the FAMES Academy's role as the primary educator for Europe's next generation of microelectronics talent.

'Demystifying the Path to Adoption'

"To shape the future of advanced FD-SOI technologies, we must train skilled engineers to build a sovereign microelectronics industry," said Laurent Fesquet, FAMES Academy leader and deputy director of the TIMA Laboratory, Grenoble INP-UGA.

"Our goal with this workshop is to demystify the path to adoption. Whether you are a startup looking to prototype a secure IoT device or a fabless company exploring 3D integration, we are opening the doors to our design kits and training programs. This is your opportunity to join an ecosystem that is actively shaping the future of European microelectronics," said Susana Bonnetier, FAMES Pilot Line open access chairperson at CEA-Leti.

During this year CEA-Leti LID World Summit, the FAMES team also will host a booth where attendees can meet the project coordinators and explore the full range of semiconductor technologies available within the pilot line.

Event Details

- **Event:** FAMES Academy Workshop: "[The FAMES Payoff Begins](#)"
Date: June 24, 2026 – 9h30-12h00
Location: Minatec, Grenoble, France
Context: Part of the CEA-Leti LID World Summit 2026
- **Registration:** [here](#)



Dominique Noguét, coordinator of the FAMES Pilot Line and CEA-Leti vice president, updated LID World Summit attendees in 2025.

Credit: Lory Vuillard / CEA

About FAMES Pilot Line

The FAMES project (“FD-SOI Pilot Line for Applications with NVM Memories, RF and 3D integration, to ensure European Sovereignty”) is a major European initiative establishing a pilot line for advanced semiconductor technologies. Funded under the European Chips Act, FAMES focuses on FD-SOI, embedded non-volatile memories, 3D integration, and RF components to ensure European technological sovereignty. The FAMES Academy is the project's educational arm, dedicated to training the workforce required to sustain this ecosystem.

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